



ZXTN19020DFF

20V NPN HIGH GAIN POWER TRANSISTOR

Features

- BV_{CEO} > 20V
- I_C = 6.5A Continuous Collector Current
- Very Low Saturation Voltage V_{CE(sat)} < 30mV @ 1A
- R_{CE(sat)} = 18mΩ
- High h_{FE} Min 260 @ 2A
- 1.5W Power Dissipation
- High Forward Blocking Voltage
- Complementary PNP Type: ZXTP19020DFF
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 and 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description

Advanced process capability has been used to maximize the performance of this transistor. The SOT23F package is compatible with the industry standard SOT23 footprint but offers lower profile and higher dissipation for applications where power density is of utmost importance.

Mechanical Data

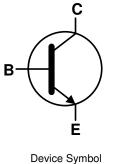
- Case: SOT23F
- Case Material: Molded Plastic. "Green" Molding Compound
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.012 grams (Approximate)

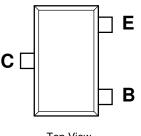
Applications

- MOSFET and IGBT Gate Drivers
- LED Driver
- Strobe Flash
- Motor Drive
- Micro Buffers



Top View





Top View Pin Configuration

Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN19020DFFTA	AEC-Q101	1E3	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

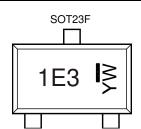
See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

<1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



1E3 = Product Type Marking Code YW = Date Code Marking Y = Year : $0 \sim 9$ \overline{W} = Week : $A \sim Z$: $1 \sim 26$ $a \sim z$: $27 \sim 52$ z represents 52 & 53 week



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	70	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEX}	70	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter-Collector Voltage (Reverse Blocking)	V _{ECO}	4.5	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	lc	6.5	A
Peak Pulse Current	ICM	20	А
Base Current	IB	1	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 5)		0.84 6.72		
Power Dissipation	(Note 6)	_	1.34 10.72	W mW/°C	
Linear Derating Factor	(Note 7)	PD PD	1.50 12.0		
	(Note 8)		2.0 16.0		
	(Note 5)		149		
	(Note 6)		93	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	- R _{0JA}	83		
	(Note 8)		60	1	
Thermal Resistance, Junction to Lead	(Note 9)	R _{θJL}	43.77	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.

7. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.

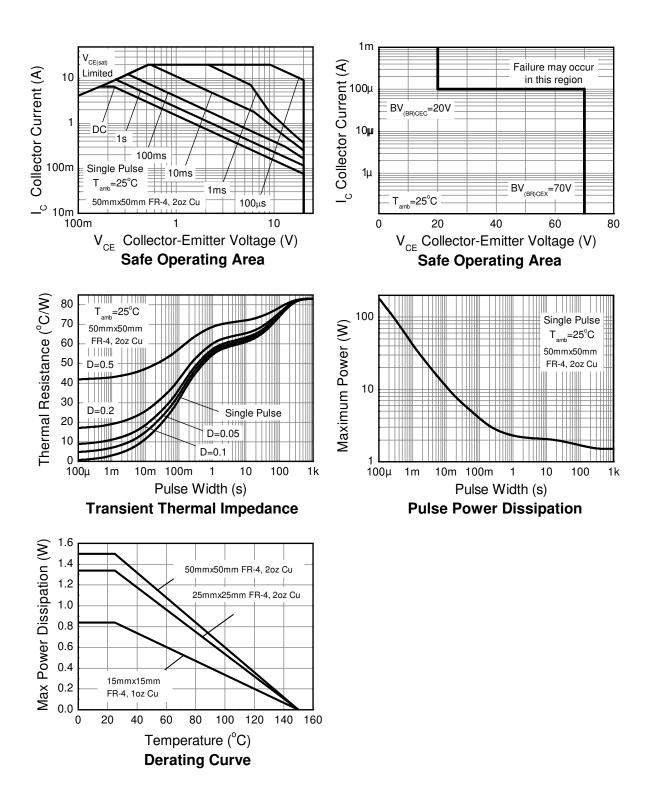
8. Same as Note 7, whilst measured at t < 5 seconds.

9. Thermal resistance from junction to solder-point (at the end of the collector lead).

10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





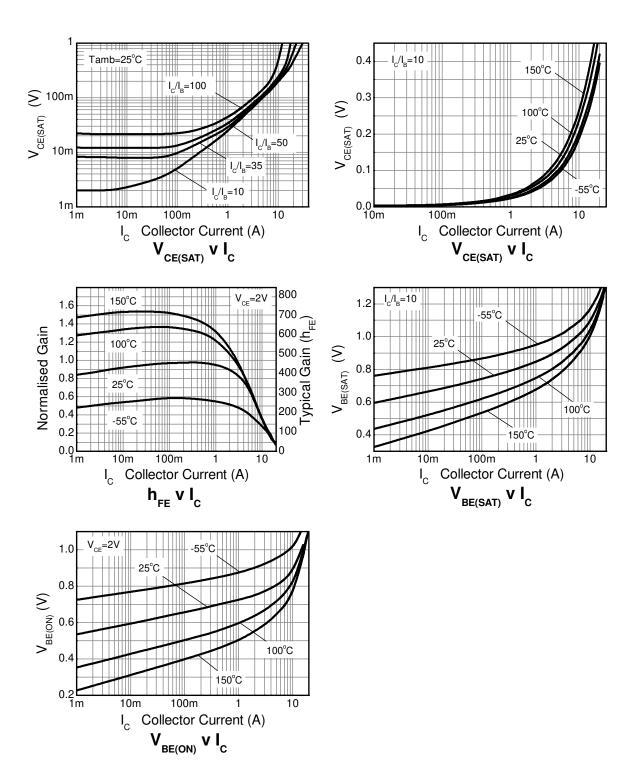
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	70	100	—	V	$I_{\rm C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Forward Blocking)	BV _{CEX}	70	100	_	V	$I_{C} = 100 \mu A; R_{BC} < 1 k \Omega \text{ or} \\ -1 V < V_{BE} < 0.25 V$
Collector-Emitter Breakdown Voltage (Base Open) (Note 11)	BV _{CEO}	20	30	—	V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.4	_	V	I _E = 100μA
Emitter-Collector Breakdown Voltage (Reverse Blocking)	BV _{ECX}	6	8.4	-	V	$I_E = 100 \mu A; R_{BC} \le 1 k \Omega \text{ or} \\ -0.25 V < V_{BC} < 0.25 V$
Emitter-Collector Breakdown Voltage (Base Open)	BV _{ECO}	4.5	5.7	_	V	I _E = 100μA
Collector-Base Cut-Off Current	I _{CBO}	_	<1 —	50 20	nA μA	V _{CB} = 56V V _{CB} = 56V, T _A = +100°C
Collector-Emitter Cut-Off Current	I _{CEX}	_	—	100	nA	V_{CE} = 56V; $R_{BE} \leq 1 k \Omega$ or -1V < V_{BE} < 0.25V
Emitter-Base Cut-Off Current	I _{EBO}	_	<1	50	nA	V _{EB} = 5.6V
ON CHARACTERISTICS (Note 11)						
Static Forward Current Transfer Ratio	h _{FE}	300 260 160 50	450 420 270 80	900 — — —	_	$\begin{split} & I_{C} = 0.1A, V_{CE} = 2V \\ & I_{C} = 2A, V_{CE} = 2V \\ & I_{C} = 6.5A, V_{CE} = 2V \\ & I_{C} = 15A, V_{CE} = 2V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	25 45 70 55 140	30 65 95 75 190	mV	$\label{eq:loss} \begin{array}{l} I_{C} = 1A, \ I_{B} = 100 \text{mA} \\ I_{C} = 1A, \ I_{B} = 10 \text{mA} \\ I_{C} = 2A, \ I_{B} = 20 \text{mA} \\ I_{C} = 2A, \ I_{B} = 40 \text{mA} \\ I_{C} = 6.5 \text{A}, \ I_{B} = 180 \text{mA} \end{array}$
Base-Emitter Saturation Voltage	V _{BE(sat)}		940	1050	mV	$I_{\rm C} = 6.5 {\rm A}, I_{\rm B} = 180 {\rm mA}$
Base-Emitter On Voltage	V _{BE(on)}	—	830	950	mV	$I_C=6.5A,\ V_{CE}=2V$
SMALL SIGNAL CHARACTERISTICS			r	r	-	-
Transition Frequency	f _T	—	160	—	MHz	$ I_{C} = 50 mA, V_{CE} = 5V, \\ f = 50 MHz $
Input Capacitance	Cibo	—	297	—	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	Cobo		32.6	40	pF	$V_{CB} = 10V, f = 1MHz$
Delay Time	t _d	—	129	—	ns	101/
Rise Time	tr		96		ns	$-V_{CC} = 10V,$ $-I_{C} = 1A,$
Storage Time	ts	—	398	—	ns	$-I_{B1} = -I_{B2} = 10 \text{mA}$
Fall Time	t _f	—	90	—	ns	

Note: 11. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

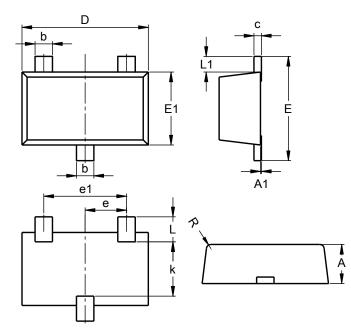




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23F

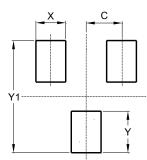


SOT23F						
Dim	Min	Max	Тур			
Α	0.80	1.00	0.90			
A1	0.00	0.10	0.01			
b	0.35	0.50	0.44			
С	0.10	0.20	0.16			
D	2.80	3.00	2.90			
е	0.95 REF					
e1	1.90 REF					
E	2.30	2.50	2.40			
E1	1.50	1.70	1.65			
k	1.20	-	-			
L	0.30	0.65	0.50			
L1	0.30	0.50	0.40			
R	0.05	0.15	-			
A	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23F



Dimensions	Value (in mm)		
С	0.95		
Х	0.80		
Y	1.110		
Y1	3.000		



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